Vishay Semiconductors



Hyperfast Rectifier, 2 x 3 A FRED Pt®



DESIGN SUPPORT TOOLS AVAILABLE



PRIMARY CHARACTERISTICS			
I _{F(AV)}	2 x 3 A		
V _R	100 V		
V _F at I _F	0.75 V		
t _{rr} (typ.)	20 ns		
T _J max.	175 °C		
Package	SlimDPAK (TO-252AE)		
Circuit configuration	Common cathode		

FEATURES

- Hyperfast recovery time
- Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- Very low profile typical height of 1.3 mm
- 175 °C operating junction temperature
- Ideal for automated placement
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Polyimide passivation for high reliability standard
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V _{RRM}		100	V
per	per leg		Total device, rated V_{R} , T_{C} = 166 °C	3	
Average rectified forward current	per device	I _{F(AV)}		6	А
Non-repetitive peak surge current	per leg	I _{FSM}	T_J = 25 °C, 10 ms sine pulse wave	70	
Operating junction and storage terr	peratures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	100	-	-		
Forward voltage V _F		I _F = 3 A	-	0.9	1.04	.,	
	V _F	I _F = 3 A, T _J = 150 °C	-	0.75	0.82	V	
		I _F = 6 A	-	1	1.2		
	I _F = 6 A, T _J = 150 °C	-	0.85	1.01			
Reverse leakage current I _R		V _R = V _R rated	-	-	5		
	'R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80	μA	
Junction capacitance	CT	V _R = 100 V	-	12	-	pF	

Revision: 08-Jul-2019

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Document Number: 96089

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	20	-	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{RR} = 0.25 A		-	-	25	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns
		T _J = 125 °C	I _F = 3 A dI _F /dt = 200 A/μs	-	26	-	
Peak recovery current		T _J = 25 °C		-	1.8	-	А
Peak recovery current I _{RRM}	T _J = 125 °C	$V_{\rm R} = 160 \text{ V}$	-	3.2	-		
	T _J = 25 °C		-	15	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	41	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾⁽²⁾		-	75	90	°C/W
Thermal resistance, junction to case per leg	R _{thJC} ⁽³⁾		-	3.2	4	°C/W
Marking device		Case style SlimDPAK (TO-252AE)		6CV	'H01	

Notes

 $^{(1)}$ The heat generated must be less than thermal conductivity from junction-to-ambient; $dP_D/dT_J < 1R_{thJA}$

⁽²⁾ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} junction to ambient

⁽³⁾ Mounted on infinite heatsink

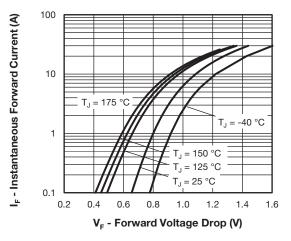


Fig. 1 - Typical Forward Voltage Drop Characteristics

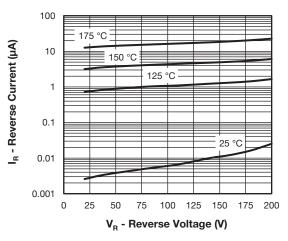


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

VS-6CVH01HM3

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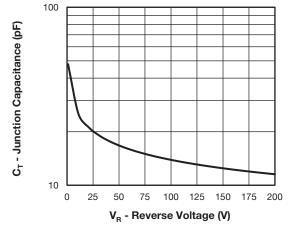


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

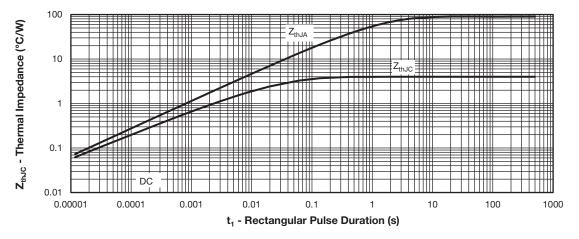
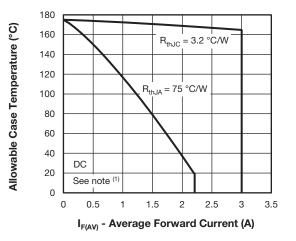
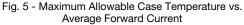


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \text{forward power loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \text{ at } (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \text{ (see fig. 6);} \\ \mathsf{Pd}_{\mathsf{REV}} = \text{inverse power loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} (1 - \mathsf{D}); \, \mathsf{I}_{\mathsf{R}} \text{ at } \mathsf{V}_{\mathsf{R1}} = \text{rated } \mathsf{V}_{\mathsf{R}} \end{array}$

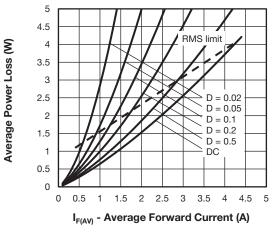


Fig. 6 - Forward Power Loss Characteristics

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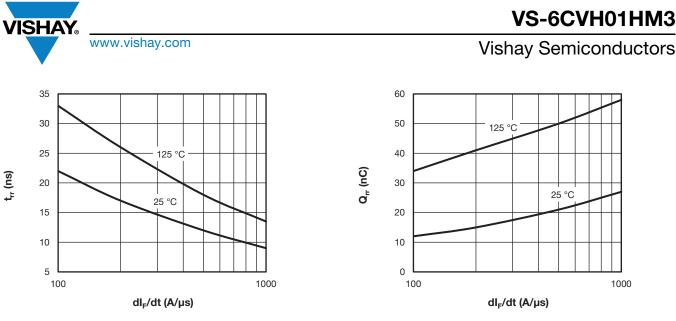


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt



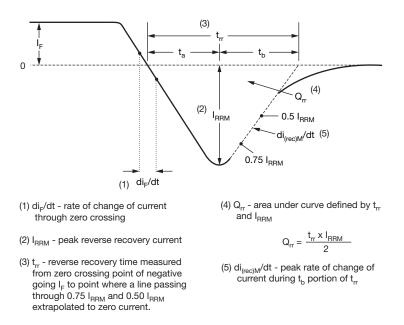
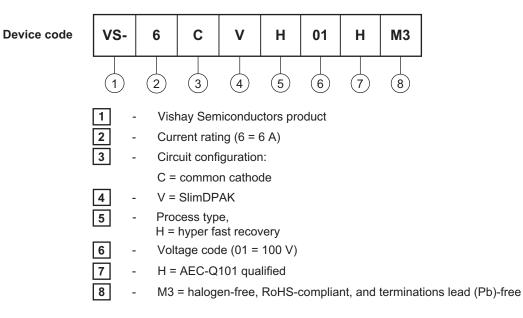


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-6CVH01HM3/I	4500	4500	13"diameter plastic tape and reel		

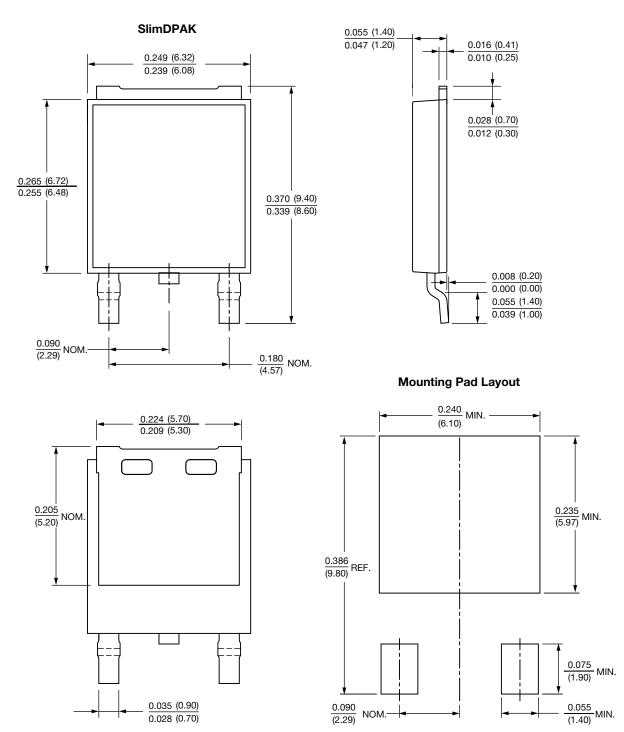
LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96081				
Part marking information	www.vishay.com/doc?96085			
Packaging information	www.vishay.com/doc?88869			





SlimDPAK

DIMENSIONS in inches (millimeters)





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